

In accordance with the guidelines and waived provisions of 37 C.F.R. 1.121 promulgated in the USPTO announcement of January 31, 2003, please make the following amendments.

IN THE CLAIMS:

Please amend the claims as follows.

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1. (Currently Amended) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and
a driver circuit comprising a plurality of thin film transistors for driving said plurality of switching elements,
wherein each of said plurality of thin film transistors comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film.
2. (Previously Amended) The active matrix display device according to claim 1 wherein said gate electrode is located over said semiconductor layer.
3. (Previously Amended) The active matrix display device according to claim 1 wherein all of said plurality of thin film transistors are p-channel transistors.
4. (Previously Amended) The active matrix display device according to claim 1 wherein all of said plurality of thin film transistors are n-channel transistors.
5. (Previously Amended) The active matrix display device according to claim 1 wherein said substrate is a glass substrate.
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6. (Previously Amended) The active matrix display device according to claim 1 wherein said crystallized semiconductor layer comprises silicon.

7. (Currently Amended) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and
a driver circuit comprising a plurality of thin film transistors for driving said plurality of switching elements, wherein each of said plurality of thin film transistors comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film,

wherein said crystallized semiconductor layer has source and drain regions and at least one lightly doped region.

8. (Previously Amended) The active matrix display device according to claim 7 wherein said substrate is a glass substrate.

9. (Previously Amended) The active matrix display device according to claim 7 wherein said source and drain regions and said at least one lightly doped region are doped with phosphorus.

10. (Canceled)

11. (Previously Amended) The active matrix display device according to claim 7 wherein said gate electrode is located over said semiconductor layer.

12. (Original) The active matrix display device according to claim 7 wherein said gate electrode is located over said semiconductor layer.

13. (Currently Amended) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and
a CMOS circuit comprising at least one n-channel thin film transistor and one p-channel thin film transistor,

wherein each of said n-channel and p-channel thin film transistors comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film.

14. (Previously Amended) The active matrix display device according to claim 13 wherein said substrate is a glass substrate.

15. (Previously Amended) The active matrix display device according to claim 13 wherein said gate electrode is located over said semiconductor layer.

16. (Previously Amended) The active matrix display device according to claim 13 wherein said crystallized semiconductor layer comprises silicon.

17. (Currently Amended) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;

a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and

a CMOS circuit comprising at least one n-channel thin film transistor and one p-channel thin film transistor, each of said first and second thin film transistors comprising a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film,

wherein said crystallized semiconductor layer has source and drain regions and at least one lightly doped region.

18. (Previously Amended) active matrix display device according to claim 17 wherein said substrate is a glass substrate.

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Cont 19. (Currently Amended) An active matrix display device comprising:

a substrate having an insulating surface;

a plurality of pixel electrodes arranged in a matrix form over said substrate;

a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;

a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and

a driver circuit comprising a plurality of thin film transistors for driving said plurality of switching elements,

wherein each of the film transistors of said switching elements and said driver circuit comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film.

20. (Previously Amended) The active matrix display device according to claim 19 wherein said gate electrode is located over said semiconductor layer.

21. (Previously Amended) The active matrix display device according to claim 19 wherein all of said plurality of thin film transistors are p-channel transistors.

22. (Previously Amended) The active matrix display device according to claim 19 wherein all of said plurality of thin film transistors are n-channel transistors.

23. (Previously Amended) The active matrix display device according to claim 19 wherein said substrate is a glass substrate.

24. (Previously Amended) The active matrix display device according to claim 19 wherein said crystallized semiconductor layer comprises silicon.

25. (Currently Amended) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and
a driver circuit comprising a plurality of thin film transistors for driving said plurality of switching elements,
wherein each of the thin film transistors of the switching elements and the driver circuit comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film,
wherein said crystallized semiconductor layer has source and drain regions and at least one lightly doped region.

26. (Previously Amended) The active matrix display device according to claim 25 wherein said substrate is a glass substrate.

27. (Previously Amended) The active matrix display device according to claim 25 wherein said source and drain regions and said at least one lightly doped region are doped with phosphorus.

28. (Canceled)

29. (Previously Amended) The active matrix display device according to claim 25 wherein said gate electrode is located over said semiconductor layer.

30. (Previously Amended) The active matrix display device according to claim 25 wherein said crystallized semiconductor layer comprises silicon.

31. (Currently Amended) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and
a CMOS circuit comprising at least one n-channel thin film transistor and one p-channel thin film transistor,

wherein each of the film transistors of the switching elements and said n-channel and p-channel thin film transistors comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film.

32. (Previously Amended) The active matrix display device according to claim 31 wherein said substrate is a glass substrate.

33. (Previously Amended) The active matrix display device according to claim 31 wherein said gate electrode is located over said semiconductor layer.

34. (Previously Amended) The active matrix display device according to claim 31 wherein said crystallized semiconductor layer comprises silicon.

35. (Currently Amended) An active matrix display device comprising:
a substrate having an insulating surface;
a plurality of pixel electrodes arranged in a matrix form over said substrate;
a plurality of switching elements operationally connected to said pixel electrodes, each of said switching elements comprising a thin film transistor;
a display medium comprising an emissive material and capable of electrically changing luminous strength disposed at each of said pixel electrodes; and
a CMOS circuit comprising at least one n-channel thin film transistor and one p-channel thin film transistor,

wherein each of the film transistors of the switching elements and said n-channel and p-channel thin film transistors comprises a crystallized semiconductor layer, a gate insulating film adjacent to said crystallized semiconductor layer and a gate electrode adjacent to said gate insulating film, and said crystallized semiconductor layer has source and drain regions and at least one lightly doped region.

36. (Previously Amended) The active matrix display device according to claim 35 wherein said substrate is a glass substrate.

37. (Previously Amended) The active matrix display device according to claim 35 wherein said crystallized semiconductor layer comprises silicon.

38. (Previously Amended) The active matrix display device according to claim 17 wherein said crystallized semiconductor layer comprises silicon.